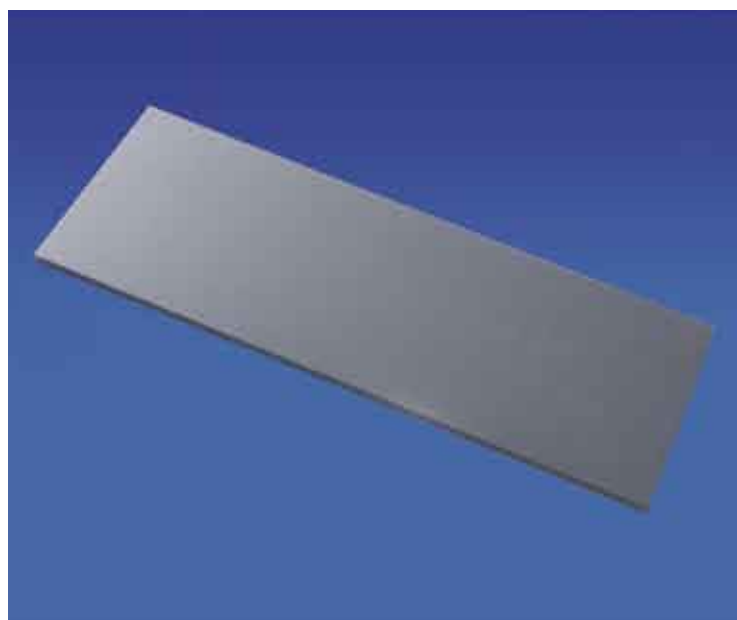


高移動度酸化物半導体ターゲット(開発中)

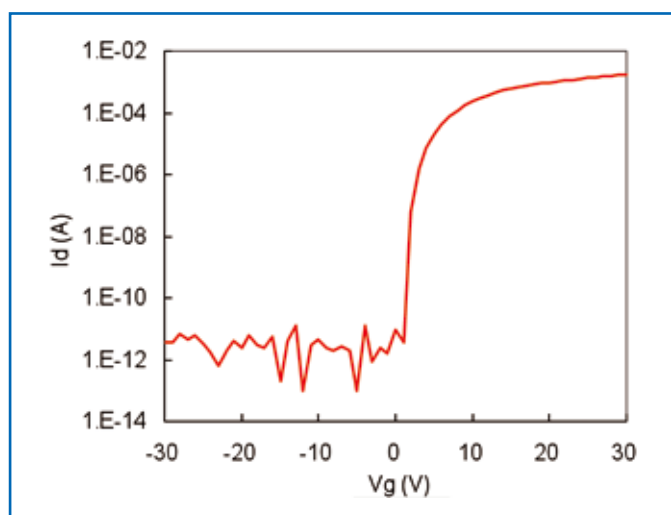
Oxide Semiconductor Sputtering Targets with High Mobility under Development

■KOS-H07 characteristics (ESL-TYPE)

	KOS-H07
Density	≥90%
Resistivity	$1.5 \times 10^{-2} \Omega \cdot \text{cm}$
Purity	4N
Mobility	≥50 cm^2/Vs
SS	0.23 V/dec
LNBTS	1.75 V

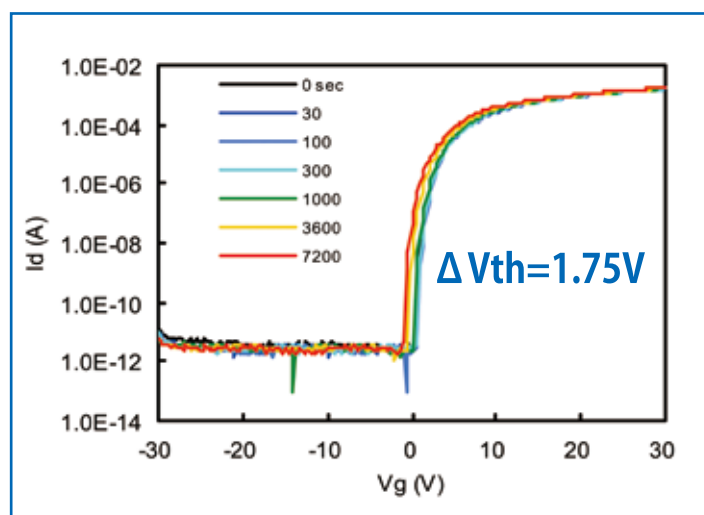


Id-Vg



$\mu_{\text{sat}} = 62.9 \text{ cm}^2/\text{Vs}$
 $V_{\text{th}} = 3.0 \text{ V}$
 $SS = 0.23 \text{ V/dec}$
 *GI: thermal SiO₂

LNBTS



Measurement condition:
 $V_g = -20\text{V}$, $V_d = 10\text{V}$, 60°C ,
 White LED (25000nit), 2hrs,
 Exposure from the top side of TFT